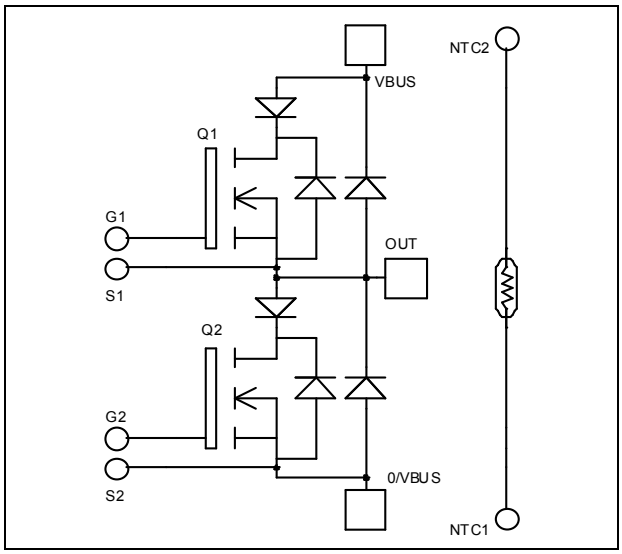
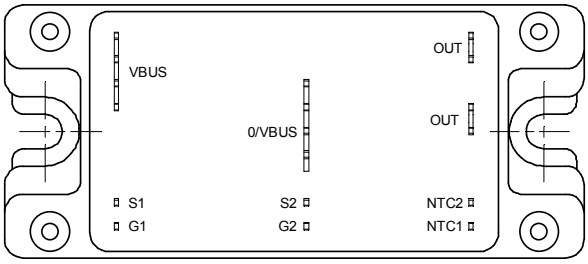
APTC90AM60SCTG

Phase leg
Series & SiC parallel diodes
Super Junction
MOSFET Power Module

V_{DSS} = 900V
R_{DSon} = 60mΩ max @ Tj = 25°C
I_D = 59A @ Tc = 25°C





Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- COOLMOS Power Semiconductors
  - Ultra low R_{DSon}
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
- ***Parallel SiC Schottky Diode***
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature Independent switching behavior
  - Positive temperature coefficient on VF
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		900	V
I_D	Continuous Drain Current	T_c = 25°C	59	A
		T_c = 80°C	44	
I_{DM}	Pulsed Drain current		150	
V_{GS}	Gate - Source Voltage		±20	V
R_{DSon}	Drain - Source ON Resistance		60	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	462	W
I_{AR}	Avalanche current (repetitive and non repetitive)		8.8	A
E_{AR}	Repetitive Avalanche Energy		2.9	mJ
E_{AS}	Single Pulse Avalanche Energy		1940	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V,V_{DS} = 900V	T_j = 25°C			200	µA
		V_{GS} = 0V,V_{DS} = 900V	T_j = 125°C		1000		
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 52A			50	60	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 6mA		2.5	3	3.5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0V				200	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{iss}	Input Capacitance	V_{GS} = 0V ; V_{DS} = 100V f = 1MHz		13.6		nF
C_{oss}	Output Capacitance			0.66		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 400V I_D = 52A		540		nC
Q_{gs}	Gate – Source Charge			64		
Q_{gd}	Gate – Drain Charge			230		
$T_{d(on)}$	Turn-on Delay Time	**Inductive Switching (125°C)** V_{GS} = 10V V_{Bus} = 600V I_D = 52A R_G = 3.8Ω		70		ns
T_r	Rise Time			20		
$T_{d(off)}$	Turn-off Delay Time			400		
T_f	Fall Time			25		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 10V ; V_{Bus} = 600V I_D = 52A ; R_G = 3.8Ω		1.8		mJ
E_{off}	Turn-off Switching Energy			1.5		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 10V ; V_{Bus} = 600V I_D = 52A ; R_G = 3.8Ω		2.52		mJ
E_{off}	Turn-off Switching Energy			1.7		

Series diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=200V	T_j = 25°C			350	µA
			T_j = 125°C			600	
I_F	DC Forward Current		T_c = 85°C		60		A
V_F	Diode Forward Voltage	I_F = 60A			1.1	1.15	V
		I_F = 120A			1.4		
		I_F = 60A	T_j = 125°C		0.9		
t_{rr}	Reverse Recovery Time	I_F = 60A V_R = 133V di/dt = 400A/µs	T_j = 25°C		24		ns
			T_j = 125°C		48		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		66		nC
			T_j = 125°C		300		

SiC parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1200V	T_j = 25°C		64	400	µA
			T_j = 175°C		112	2000	
I_F	DC Forward Current		Tc = 100°C		20		A
V_F	Diode Forward Voltage	I_F = 20A	T_j = 25°C		1.6	1.8	V
			T_j = 175°C		2.3	3	
Q_C	Total Capacitive Charge	I_F = 20A, V_R = 600V di/dt =1000A/µs			80		nC
C	Total Capacitance	f = 1MHz, V_R = 200V			192		pF
		f = 1MHz, V_R = 400V			138		

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance	Transistor				0.27	°C/W
		Series diode				0.65	
		SiC Parallel diode				1	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			4000			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

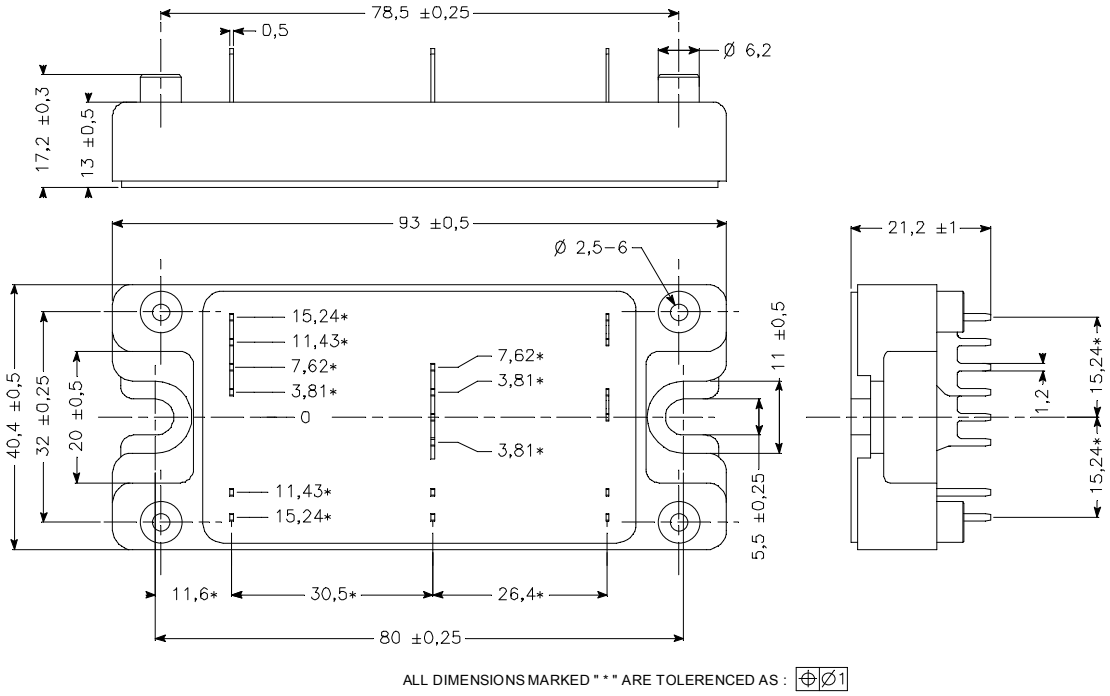
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
ΔB/B		T_C=100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

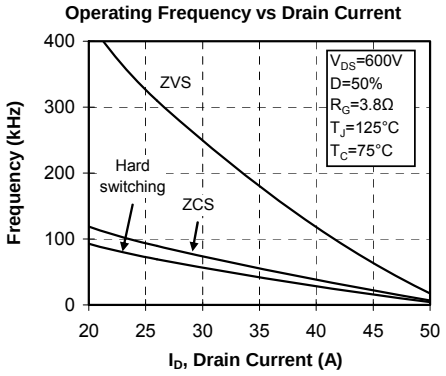
T: Thermistor temperature
R_T: Thermistor value at T

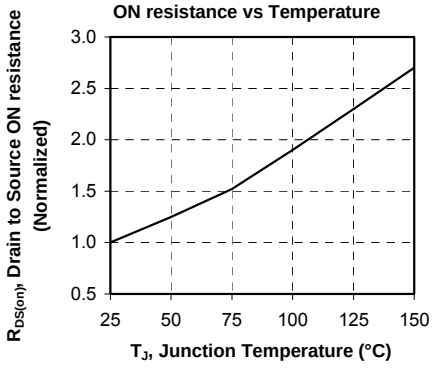
SP4 Package outline (dimensions in mm)

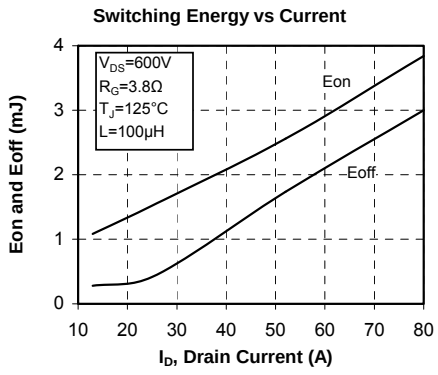


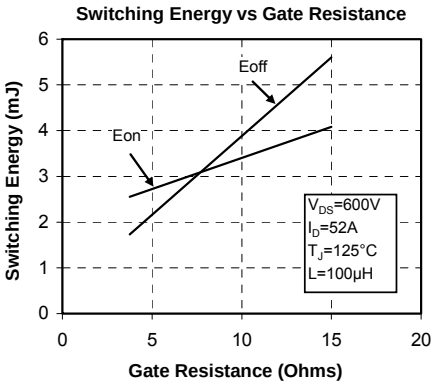
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical CoolMOS Performance Curve

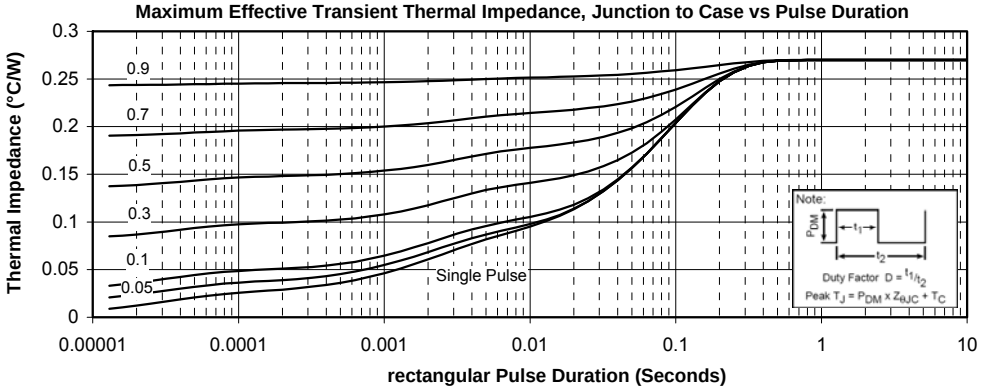




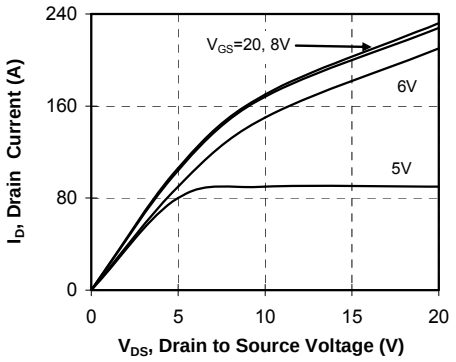




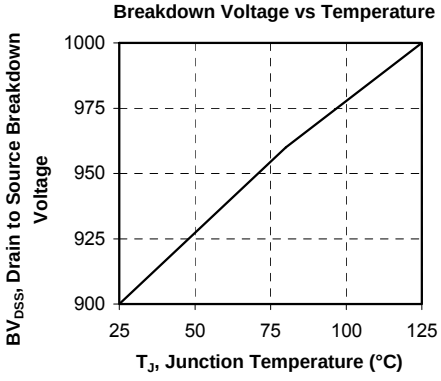
Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



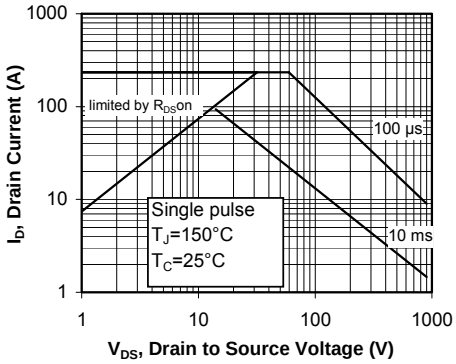
Low Voltage Output Characteristics



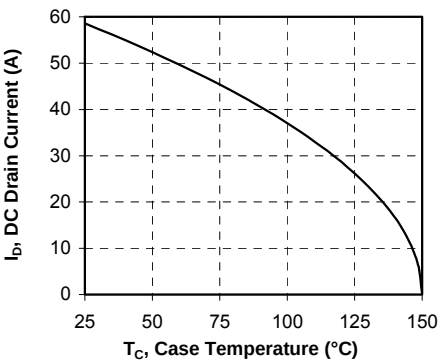
Breakdown Voltage vs Temperature



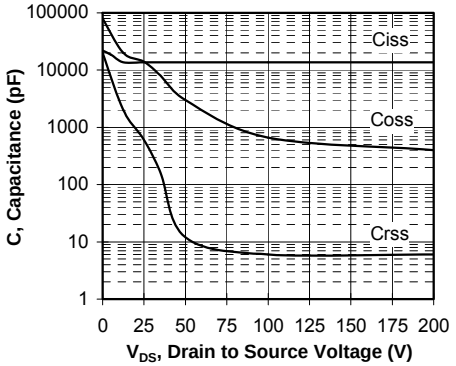
Maximum Safe Operating Area



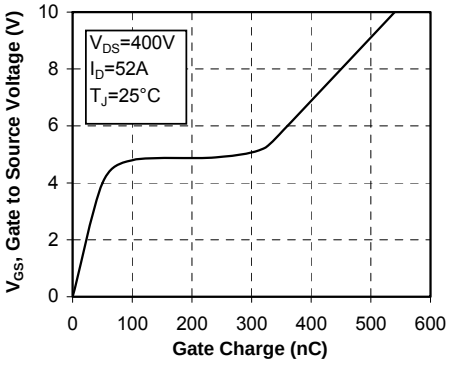
DC Drain Current vs Case Temperature



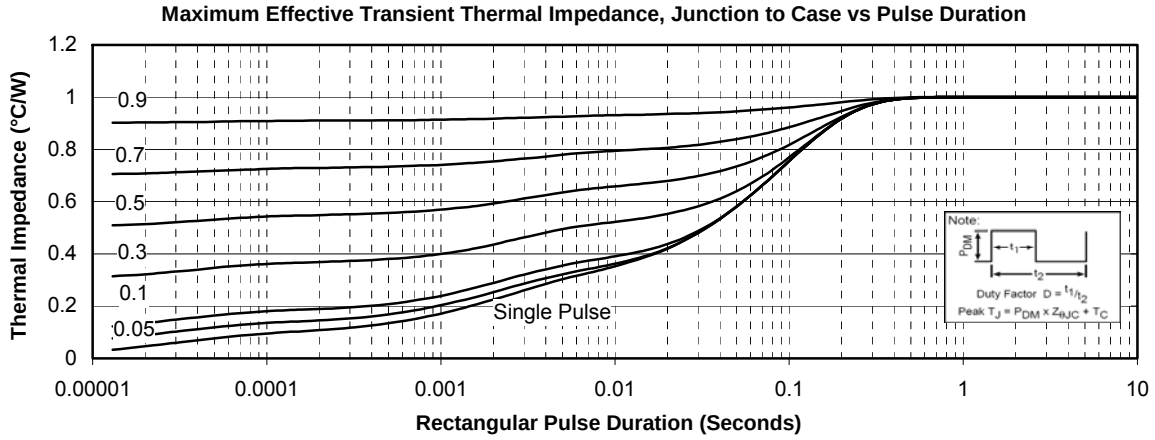
Capacitance vs Drain to Source Voltage

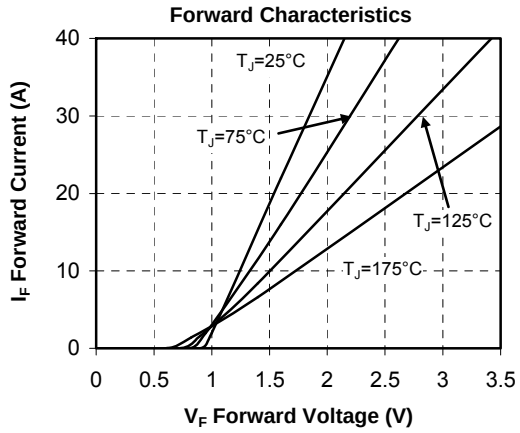


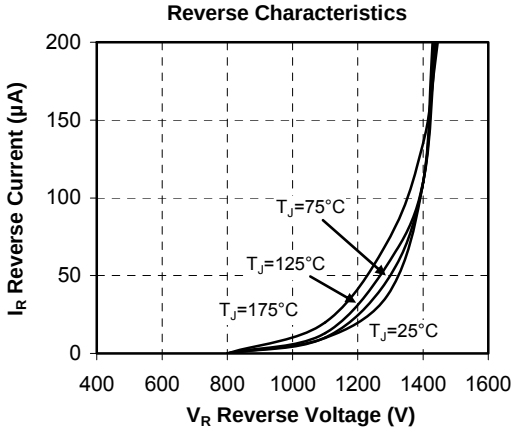
Gate Charge vs Gate to Source Voltage

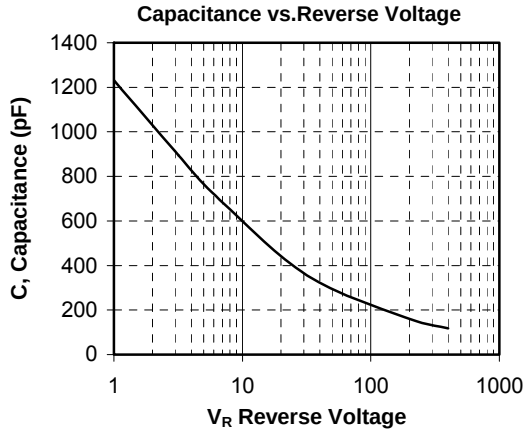


Typical parallel SiC Diode Performance Curve









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